## MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

**PLED** 

# Broduct data sheet







- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

#### TRANSISTOR (PNP)

#### **FEATURES**

- Epitaxial planar die construction
- Complementary NPN Type available(MMBT2222A-

Marking: 2F

#### MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit	
V <sub>CBO</sub>	Collector-Base Voltage	-60	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	٧	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
Ic	Collector Current -Continuous	-600	mA	
P <sub>D</sub>	Total Device Dissipation	250	mW	
R <sub>0JA</sub>	Thermal Resistance Junction to Ambient	500	°C/W	
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55 to +150	℃	

**ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)** 

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I <sub>C</sub> =-10μΑ,I <sub>E</sub> =0	-60			<b>V</b>
Collector-emitter breakdown voltage	$V_{(BR)CEO^*}$	I <sub>C</sub> =-10mA,I <sub>B</sub> =0	-60			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10μΑ,I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-50V,I <sub>E</sub> =0			-20	nA
Base cut-off current	I <sub>EBO</sub>	$V_{EB}$ =-3 $V$ , $I_{C}$ =0			-10	nA
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> =-30 V, V <sub>BE(off)</sub> =-0.5V			-50	nA
	h <sub>FE(1)</sub>	V <sub>CE</sub> =-10V,I <sub>C</sub> =-150mA	100		300	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =-10V,I <sub>C</sub> =-0.1mA	75			
DC current gain	h <sub>FE(3)</sub>	V <sub>CE</sub> =-10V,I <sub>C</sub> =-1mA	100			
	h <sub>FE(4)</sub>	V <sub>CE</sub> =-10V,I <sub>C</sub> =-10mA	100			
	h <sub>FE(5)</sub>	V <sub>CE</sub> =-10V,I <sub>C</sub> =-500mA	50			
Collector-emitter saturation voltage	V <sub>CE(sat)*</sub>	I <sub>C</sub> =-150mA,I <sub>B</sub> =-15mA			-0.4	V
Conector-enlitter saturation voltage	V <sub>CE(sat)*</sub>	I <sub>C</sub> =-500mA,I <sub>B</sub> =-50mA			-1.6	V
Page emitter esturation voltage	V <sub>BE(sat)*</sub>	I <sub>C</sub> =-150mA,I <sub>B</sub> =-15mA			-1.3	>
Base-emitter saturation voltage	V <sub>BE(sat)*</sub>	I <sub>C</sub> =-500mA,I <sub>B</sub> =-50mA			-2.6	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-20V,I <sub>C</sub> =-50mA,f=100MHz	200			MHz
Delay time	t <sub>d</sub>				10	ns
Rise time	t <sub>r</sub>	$V_{CE}$ =-30V, $I_{C}$ =-150mA, $B_1$ =-15mA			25	ns
Storage time	ts	V <sub>CE</sub> =-6V,I <sub>C</sub> =-150mA,			225	ns
Fall time	t <sub>f</sub>	I <sub>B1</sub> =- I <sub>B2</sub> =- 15mA			60	ns

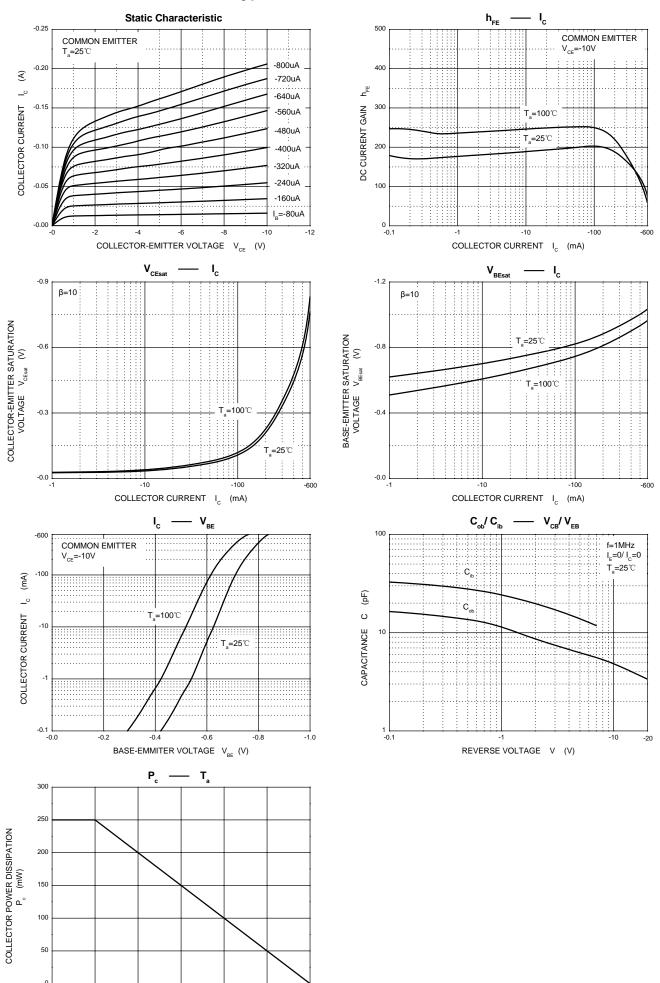
<sup>\*</sup>Pulse test: t<sub>p</sub>≤300μs, δ≤0.02.



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#### Compiance

#### **Typical Characteristics**



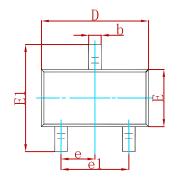
AMBIENT TEMPERATURE T (℃)

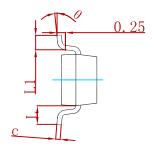


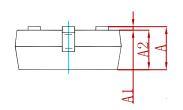
#### Semiconductor

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#### **PACKAGE MECHANICAL DATA**

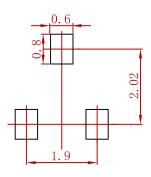






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	) TYP	0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

### **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
MMBT2907A-MS	SOT-23	3000



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